

8. (Previously Presented) A light-emitting diode according to claim 6, wherein a metal layer which reflects light to the luminous extracting side of said device is formed on said reflection plane.

9. (Previously Presented) A light-emitting diode according to claim 6, wherein said crystal growth substrate is formed by using  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1$ ) or silicon carbide (SiC).

10. (Currently Amended) A light-emitting diode according to claim 6, wherein a taper plane which inclines to said crystal growth plane of said crystal growth substrate is formed at least as a portion of at least one of said output plane or at least as a portion of said reflection plane.

11. (Canceled)

12. (Canceled)

13. (Canceled)

14. (Canceled)

15. (Canceled)

16. (Canceled)

17. (Canceled)

18. (Canceled)

19. (Canceled)

20. (Canceled)